

Attorney Docket No. 33851/42503  
PATENT



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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicant(s): Michael David Church

Conf. No.: 8108

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Serial No.: 10/026,294

Art Unit: 2823

Filed: December 20, 2001

Examiner: Nguyen, Khiem D.

For: METHOD OF FABRICATING ENHANCED EPROM STRUCTURES  
WITH ACCENTUATED HOT ELECTRON GENERATION REGIONS

AMENDMENT

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

Please amend the above-identified application as follows:

IN THE CLAIMS

Please see the Claim Summary Document attached hereto.

REMARKS

In response to the official Office Action dated May 26, 2004, Applicant has amended the claims. Claims 1 and 13 were objected to because of the phrase "poly semiconductor layer." To avoid confusion, the word "poly" has been removed. This should remove the objection.

Claims 1-3, 6-15 and 17-21 stand rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over Claims 1-10 of US Patent 6,492,225 ('225 Patent). This rejection is respectfully traversed.

The claims of the present application and the '225 Patent are very similar, but they are not identical. Claim 1 of both the present application and the '225 Patent deals specifically with a process for making semiconductor devices in a polysilicon gate and using them in a self-aligned process to create the source and drain regions. However, they differ in that the present claimed invention includes implanting a first dopant into the well to create a first region and a second region separate from the first region. The first and second regions are implanted across the boundary of the active region and are directly spaced apart from each other across the active region and spaced apart from the center of the active region. This step